



POWER SKY (H.K.) LTD.

TO-92 Plastic-Encapsulate Transistors

M8550 TRANSISTOR (PNP)

FEATURES

Power dissipation

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-800	mA
P_C	Collector Power Dissipation	625	mW
T_J	Junction Temperature	125	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-125	$^{\circ}\text{C}$

TO-92

1. EMITTER

2. BASE

3. COLLECTOR



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

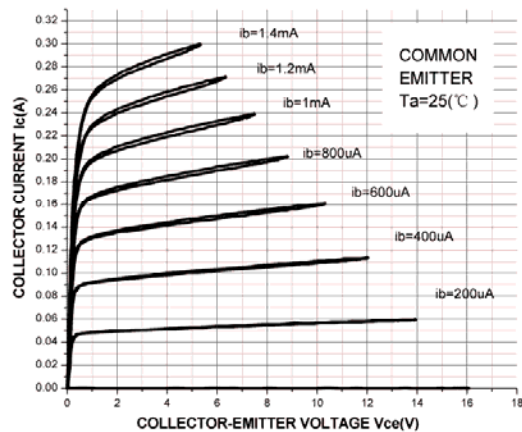
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	$I_C = -100\mu\text{A}$, $I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V(BR)_{CEO}^*$	$I_C = -0.1\text{mA}$, $I_B = 0$	-25		V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_E = -100\mu\text{A}$, $I_C = 0$	-6		V
Collector cut-off current	I_{CBO}	$V_{CB} = -35\text{V}$, $I_E = 0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20\text{V}$, $I_B = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1\text{V}$, $I_C = -5\text{mA}$	45		
	$h_{FE(2)}$	$V_{CE} = -1\text{V}$, $I_C = -100\text{mA}$	80	400	
	$h_{FE(3)}$	$V_{CE} = -1\text{V}$, $I_C = -800\text{mA}$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800\text{mA}$, $I_B = -80\text{mA}$		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800\text{mA}$, $I_B = -80\text{mA}$		-1.2	V
Transition frequency	f_T	$V_{CE} = -6\text{V}$, $I_C = -20\text{mA}$ $f = 30\text{MHz}$	150		MHz

*Pulse Test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

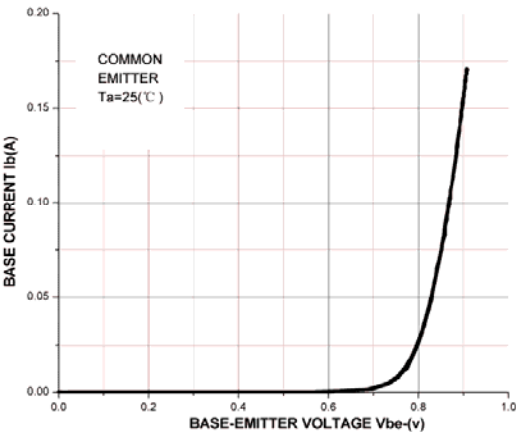
Typical Characteristics

M8550

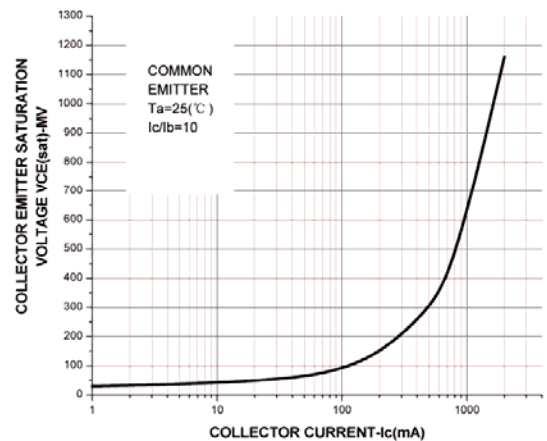
Ic-Vce



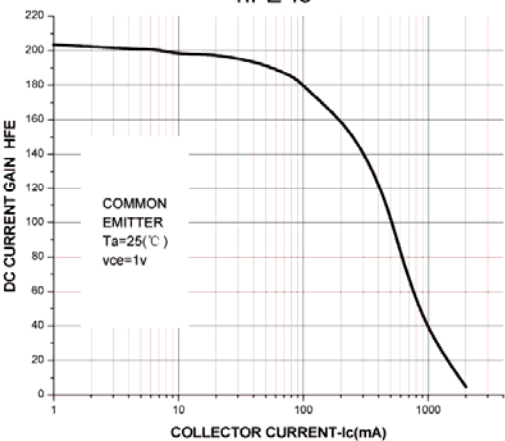
Ib-Vbe



Vcesat-Ic



hFE-Ic



Pc-Ta

